

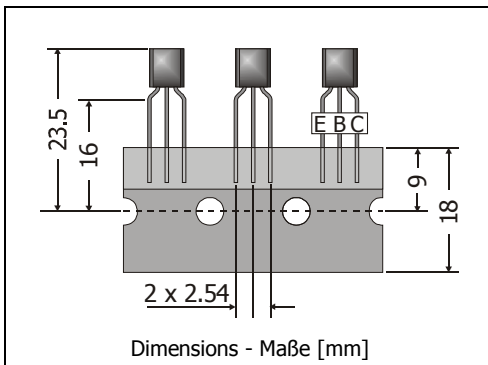
MPSA56

PNP

General Purpose Si-Epitaxial Planar Transistors
Si-Epitaxial Planar-Transistoren für universellen Einsatz

PNP

Version 2012-05-23



Power dissipation
Verlustleistung

625 mW

Plastic case
Kunststoffgehäuse

TO-92
(10D3)

Weight approx. – Gewicht ca.

0.18 g

Plastic material has UL classification 94V-0
Gehäusematerial UL94V-0 klassifiziert

Standard packaging taped in ammo pack
Standard Lieferform getupet in Ammo-Pack



Maximum ratings (T_A = 25°C)

Grenzwerte (T_A = 25°C)

			MPSA56
Collector-Emitter-volt. – Kollektor-Emitter-Spannung	B open	- V _{CEO}	80 V
Collector-Base-voltage – Kollektor-Basis-Spannung	E open	- V _{CBO}	80 V
Emitter-Base-voltage – Emitter-Basis-Spannung	C open	- V _{EBO}	4 V
Power dissipation – Verlustleistung		P _{tot}	625 mW ¹⁾
Collector current – Kollektorstrom (dc)		- I _C	500 mA
Peak Collector current – Kollektor-Spitzenstrom		- I _{CM}	1 A
Peak Base current – Basis-Spitzenstrom		- I _{BM}	200 mA
Junction temperature – Sperrschichttemperatur		T _j	-55...+150°C
Storage temperature – Lagerungstemperatur		T _s	-55...+150°C

Characteristics (T_j = 25°C)

Kennwerte (T_j = 25°C)

		Min.	Typ.	Max.
DC current gain – Kollektor-Basis-Stromverhältnis ²⁾				
- I _C = 10 mA, - V _{CE} = 1 V	h _{FE}	100	–	–
- I _C = 100 mA, - V _{CE} = 1 V	h _{FE}	100	–	–
Collector-Emitter saturation voltage – Kollektor-Emitter-Sättigungssp. ²⁾				
- I _C = 100 mA, - I _B = 10 mA	- V _{CEsat}	–	–	0.25 V
Base-Emitter voltage – Basis-Emitter-Spannung ²⁾				
- I _C = 100 mA, - V _{CE} = 1 V	- V _{BE}	–	–	1.2 V
Collector-Base cutoff current – Kollektor-Basis-Reststrom				
- V _{CB} = 80 V, (E open)	MPSA56	- I _{CBO}	–	100 nA

1 Valid, if leads are kept at ambient temperature at a distance of 2 mm from case

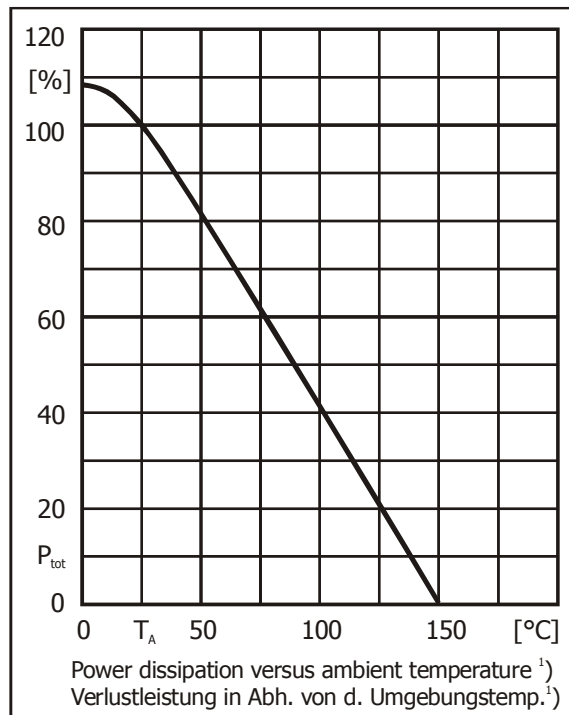
Gültig wenn die Anschlussdrähte in 2 mm Abstand vom Gehäuse auf Umgebungstemperatur gehalten werden

2 Tested with pulses t_p = 300 μs, duty cycle ≤ 2% – Gemessen mit Impulsen t_p = 300 μs, Schaltverhältnis ≤ 2%

Characteristics (T_j = 25°C)

Kennwerte (T_j = 25°C)

		Min.	Typ.	Max.
Emitter-Base cutoff current – Emitter-Basis-Reststrom - V _{EB} = 4 V, (C open)	- I _{EB0}	–	–	100 nA
Gain-Bandwidth Product – Transitfrequenz - I _C = 100 mA, - V _{CE} = 1 V, f = 100 MHz	f _T	50 MHz	–	–
Thermal resistance junction to ambient air Wärmewiderstand Sperrschicht – umgebende Luft	R _{thA}	< 200 K/W ¹⁾		
Recommended complementary NPN transistors Empfohlene komplementäre NPN-Transistoren		MPSA06		



¹ Valid, if leads are kept at ambient temperature at a distance of 2 mm from case
Gültig wenn die Anschlussdrähte in 2 mm Abstand vom Gehäuse auf Umgebungstemperatur gehalten werden